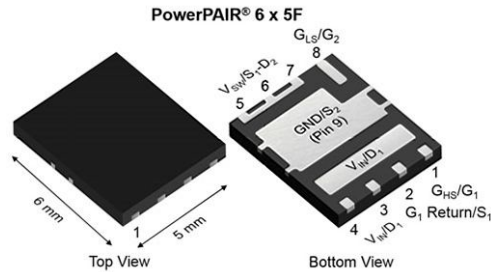


## Dual N-Channel 30 V (D-S) MOSFET



### FEATURES

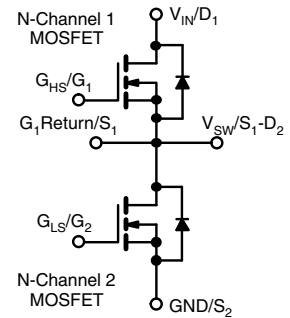
- TrenchFET® Gen IV power MOSFET
- 100 % R<sub>g</sub> and UIS tested
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)



**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**

### APPLICATIONS

- CPU core power
- Computer / server peripherals
- POL
- Synchronous buck converter
- Telecom DC/DC



PRODUCT SUMMARY		
	CHANNEL-1	CHANNEL-2
V <sub>DS</sub> (V)	30	30
R <sub>DS(on)</sub> max. (Ω) at V <sub>GS</sub> = 10 V	0.00245	0.00075
R <sub>DS(on)</sub> max. (Ω) at V <sub>GS</sub> = 4.5 V	0.00380	0.00120
Q <sub>g</sub> typ. (nC)	8.5	35
I <sub>D</sub> (A) <sup>a</sup>	88	248
Configuration	Dual	

ORDERING INFORMATION	
Package	PowerPAIR 6 x 5F
Lead (Pb)-free and halogen-free	SiZF928DT-T1-GE3

ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25 °C, unless otherwise noted)					
PARAMETER	SYMBOL	CHANNEL-1	CHANNEL-2	UNIT	
Drain-source voltage	V <sub>DS</sub>	30	30	V	
Gate-source voltage	V <sub>GS</sub>	+16, -12	+16, -12		
Continuous drain current (T <sub>J</sub> = 150 °C)	I <sub>D</sub>	T <sub>C</sub> = 25 °C	88	248	A
		T <sub>C</sub> = 70 °C	70	198	
		T <sub>A</sub> = 25 °C	33 <sup>b, c</sup>	61 <sup>b, c</sup>	
		T <sub>A</sub> = 70 °C	26 <sup>b, c</sup>	49 <sup>b, c</sup>	
Pulsed drain current (t = 100 μs)	I <sub>DM</sub>	150	400		
Continuous source-drain diode current	I <sub>S</sub>	T <sub>C</sub> = 25 °C	26	67	A
		T <sub>A</sub> = 25 °C	3.6 <sup>b, c</sup>	7.4 <sup>b, c</sup>	
Single pulse avalanche current	I <sub>AS</sub>	20	50		
Single pulse avalanche energy	E <sub>AS</sub>	20	125	mJ	
Maximum power dissipation	P <sub>D</sub>	T <sub>C</sub> = 25 °C	28	74	W
		T <sub>C</sub> = 70 °C	18	47	
		T <sub>A</sub> = 25 °C	3.9 <sup>b, c</sup>	4.5 <sup>b, c</sup>	
		T <sub>A</sub> = 70 °C	2.5 <sup>b, c</sup>	2.9 <sup>b, c</sup>	
Operating junction and storage temperature range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150		°C	
Soldering recommendations (peak temperature) <sup>d, e</sup>		260			

THERMAL RESISTANCE RATINGS							
PARAMETER	SYMBOL	CHANNEL-1		CHANNEL-2		UNIT	
		TYP.	MAX.	TYP.	MAX.		
Maximum junction-to-ambient <sup>b, f</sup>	t ≤ 10 s	R <sub>thJA</sub>	25	32	22	28	°C/W
Maximum junction-to-case (source)	Steady state	R <sub>thJC</sub>	3.5	4.4	1.3	1.7	

#### Notes

- T<sub>C</sub> = 25 °C
- Surface mounted on 1" x 1" FR4 board
- t = 10 s
- See solder profile ([www.vishay.com/doc?73257](http://www.vishay.com/doc?73257)). The PowerPAIR is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- Rework conditions: manual soldering with a soldering iron is not recommended for leadless components
- Maximum under steady state conditions is 65 °C/W for channel-1 and 65 °C/W for channel-2



<b>SPECIFICATIONS</b> ( $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted)								
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT		
<b>Static</b>								
Drain-source breakdown voltage	$V_{DS}$	$V_{GS} = 0\text{ V}, I_D = 1\text{ mA}$	Ch-1	30	-	-	V	
			Ch-2	30	-	-		
Gate-source threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	Ch-1	1	-	2	nA	
			Ch-2	1	-	2		
Gate-source leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = +16\text{ V}, -12\text{ V}$	Ch-1	-	-	$\pm 100$	nA	
		$V_{DS} = 0\text{ V}, V_{GS} = +16\text{ V}, -12\text{ V}$	Ch-2	-	-	$\pm 100$		
Zero Gate voltage drain current	$I_{DSS}$	$V_{DS} = 24\text{ V}, V_{GS} = 0\text{ V}$	Ch-1	-	-	1	$\mu\text{A}$	
			Ch-2	-	-	1		
		$V_{DS} = 24\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$	Ch-1	-	-	5		
			Ch-2	-	-	5		
On-state drain current <sup>b</sup>	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}, V_{GS} = 10\text{ V}$	Ch-1	20	-	-	A	
			Ch-2	20	-	-		
Drain-source on-state resistance <sup>b</sup>	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 10\text{ A}$	Ch-1	-	0.00180	0.00245	$\Omega$	
		$V_{GS} = 10\text{ V}, I_D = 15\text{ A}$	Ch-2	-	0.00053	0.00075		
		$V_{GS} = 4.5\text{ V}, I_D = 5\text{ A}$	Ch-1	-	0.00270	0.00380		
		$V_{GS} = 4.5\text{ V}, I_D = 10\text{ A}$	Ch-2	-	0.00082	0.00120		
Forward transconductance <sup>b</sup>	$g_{fs}$	$V_{DS} = 15\text{ V}, I_D = 40\text{ A}$	Ch-1	-	97	-	S	
		$V_{DS} = 15\text{ V}, I_D = 50\text{ A}$	Ch-2	-	175	-		
<b>Dynamic <sup>a</sup></b>								
Input capacitance	$C_{iss}$	Channel-1 $V_{DS} = 15\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	Ch-1	-	1265	-	pF	
			Ch-2	-	5650	-		
Output capacitance	$C_{oss}$		Ch-1	-	455	-		
			Ch-2	-	1796	-		
Reverse transfer capacitance	$C_{rss}$		Channel-2 $V_{DS} = 15\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	Ch-1	-	30		-
			Ch-2	-	125	-		
$C_{rss}/C_{iss}$ ratio		Ch-1	-	0.023	0.046			
		Ch-2	-	0.023	0.046			
Total gate charge	$Q_g$	$V_{DS} = 15\text{ V}, V_{GS} = 10\text{ V}, I_D = 10\text{ A}$	Ch-1	-	18.5	28	nC	
		$V_{DS} = 15\text{ V}, V_{GS} = 10\text{ V}, I_D = 10\text{ A}$	Ch-2	-	77	116		
		$V_{DS} = 15\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 10\text{ A}$	Ch-1	-	8.5	12.8		
		$V_{DS} = 15\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 10\text{ A}$	Ch-2	-	35	53		
Gate-source charge	$Q_{gs}$	Channel-1 $V_{DS} = 15\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 10\text{ A}$	Ch-1	-	3.9	-		
		Ch-2	-	17	-			
Gate-drain charge	$Q_{gd}$	Channel-2 $V_{DS} = 15\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 10\text{ A}$	Ch-1	-	1.6	-		
		Ch-2	-	5.2	-			
Output charge	$Q_{oss}$	$V_{DS} = 15\text{ V}, V_{GS} = 0\text{ V}$	Ch-1	-	13	-		
			Ch-2	-	51	-		
Gate resistance	$R_g$	$f = 1\text{ MHz}$	Ch-1	0.2	1	2	$\Omega$	
			Ch-2	0.15	0.75	1.5		



SPECIFICATIONS (T <sub>J</sub> = 25 °C, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
<b>Dynamic <sup>a</sup></b>							
Turn-on delay time	t <sub>d(on)</sub>	Channel-1 V <sub>DD</sub> = 15 V, R <sub>L</sub> = 1.5 Ω I <sub>D</sub> ≅ 10 A, V <sub>GEN</sub> = 4.5 V, R <sub>g</sub> = 1 Ω	Ch-1	-	20	40	ns
Rise time	t <sub>r</sub>		Ch-2	-	38	80	
Turn-off delay time	t <sub>d(off)</sub>	Channel-2 V <sub>DD</sub> = 15 V, R <sub>L</sub> = 3 Ω I <sub>D</sub> ≅ 10 A, V <sub>GEN</sub> = 4.5 V, R <sub>g</sub> = 1 Ω	Ch-1	-	92	185	
			Ch-2	-	95	190	
Fall time	t <sub>f</sub>	Channel-1 V <sub>DD</sub> = 15 V, R <sub>L</sub> = 3 Ω I <sub>D</sub> ≅ 10 A, V <sub>GEN</sub> = 4.5 V, R <sub>g</sub> = 1 Ω	Ch-1	-	22	45	
			Ch-2	-	46	90	
Turn-on delay time	t <sub>d(on)</sub>	Channel-2 V <sub>DD</sub> = 15 V, R <sub>L</sub> = 3 Ω I <sub>D</sub> ≅ 10 A, V <sub>GEN</sub> = 10 V, R <sub>g</sub> = 1 Ω	Ch-1	-	6	15	
			Ch-2	-	17	35	
Rise time	t <sub>r</sub>	Channel-1 V <sub>DD</sub> = 15 V, R <sub>L</sub> = 3 Ω I <sub>D</sub> ≅ 10 A, V <sub>GEN</sub> = 10 V, R <sub>g</sub> = 1 Ω	Ch-1	-	11	20	
			Ch-2	-	18	40	
Turn-off delay time	t <sub>d(off)</sub>	Channel-2 V <sub>DD</sub> = 15 V, R <sub>L</sub> = 3 Ω I <sub>D</sub> ≅ 10 A, V <sub>GEN</sub> = 10 V, R <sub>g</sub> = 1 Ω	Ch-1	-	5	10	
			Ch-2	-	48	100	
Fall time	t <sub>f</sub>	Channel-1 V <sub>DD</sub> = 15 V, R <sub>L</sub> = 3 Ω I <sub>D</sub> ≅ 10 A, V <sub>GEN</sub> = 10 V, R <sub>g</sub> = 1 Ω	Ch-1	-	22	45	
			Ch-2	-	45	90	
<b>Drain-Source Body Diode Characteristics</b>							
Continuous source-drain diode current	I <sub>S</sub>	T <sub>C</sub> = 25 °C	Ch-1	-	-	26	A
			Ch-2	-	-	67	
Pulse diode forward current <sup>a</sup>	I <sub>SM</sub>		Ch-1	-	-	150	
			Ch-2	-	-	400	
Body diode voltage	V <sub>SD</sub>	I <sub>S</sub> = 10 A, V <sub>GS</sub> = 0 V	Ch-1	-	0.78	1.1	V
		I <sub>S</sub> = 3 A, V <sub>GS</sub> = 0 V	Ch-2	-	0.75	1.1	
Body diode reverse recovery time	t <sub>rr</sub>	Channel-1 I <sub>F</sub> = 10 A, di/dt = 100 A/μs, T <sub>J</sub> = 25 °C	Ch-1	-	20	40	ns
			Ch-2	-	50	100	
Body diode reverse recovery charge	Q <sub>rr</sub>	Channel-2 I <sub>F</sub> = 10 A, di/dt = 100 A/μs, T <sub>J</sub> = 25 °C	Ch-1	-	10	20	nC
			Ch-2	-	50	100	
Reverse recovery fall time	t <sub>a</sub>	Channel-1 I <sub>F</sub> = 10 A, di/dt = 100 A/μs, T <sub>J</sub> = 25 °C	Ch-1	-	11.5	-	ns
			Ch-2	-	26	-	
Reverse recovery rise time	t <sub>b</sub>	Channel-2 I <sub>F</sub> = 10 A, di/dt = 100 A/μs, T <sub>J</sub> = 25 °C	Ch-1	-	8.5	-	
			Ch-2	-	24	-	

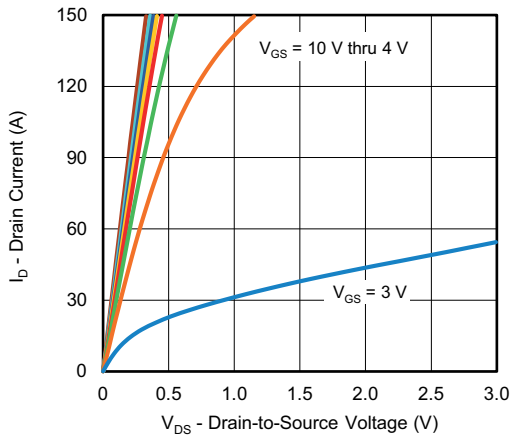
**Notes**

- a. Guaranteed by design, not subject to production testing
- b. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %

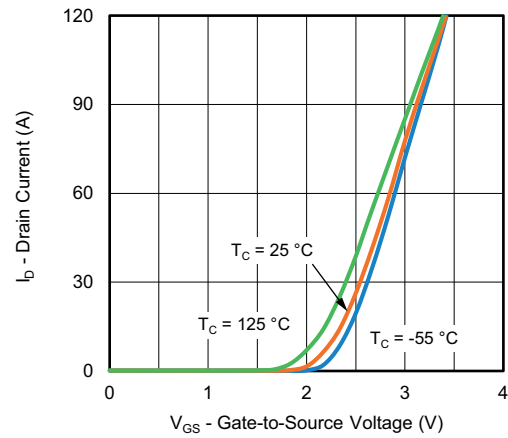
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



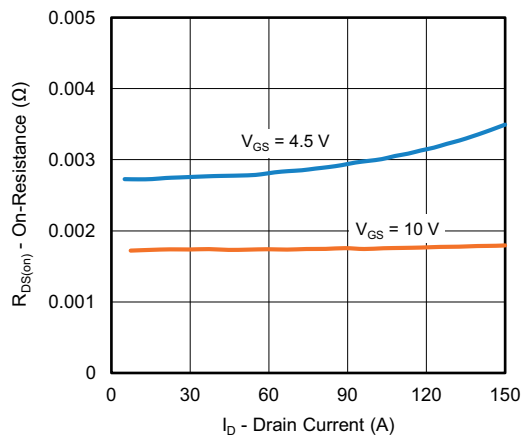
**CHANNEL-1 TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



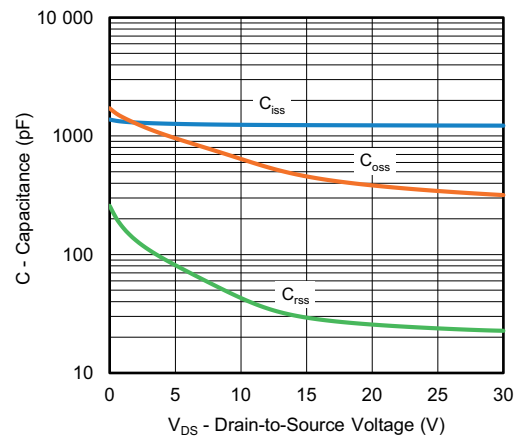
**Output Characteristics**



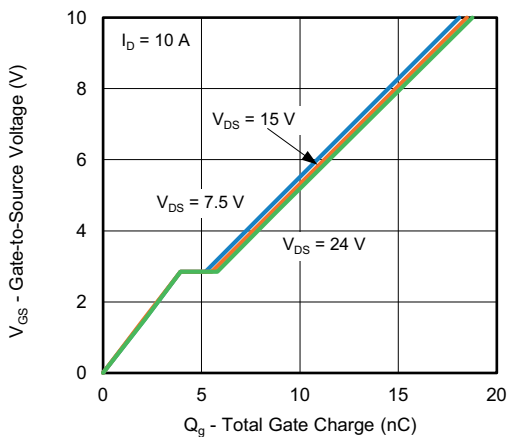
**Transfer Characteristics**



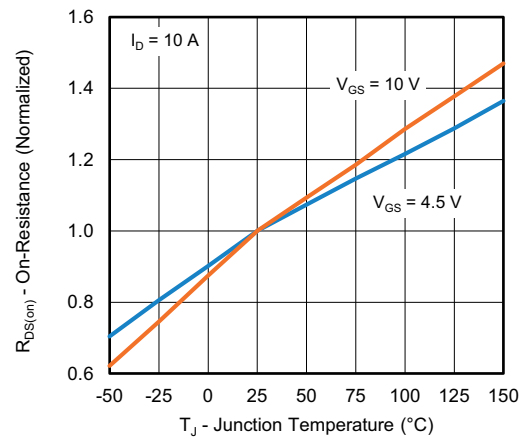
**On-Resistance vs. Drain Current**



**Capacitance**



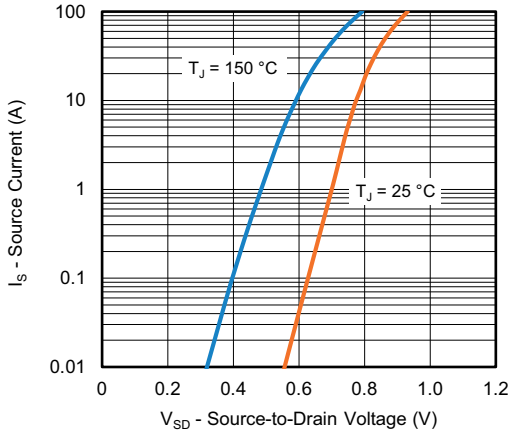
**Gate Charge**



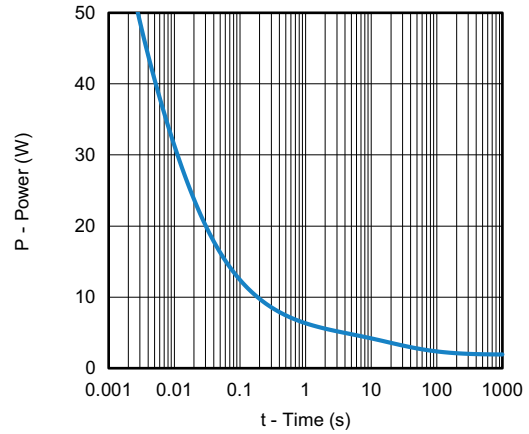
**On-Resistance vs. Junction Temperature**



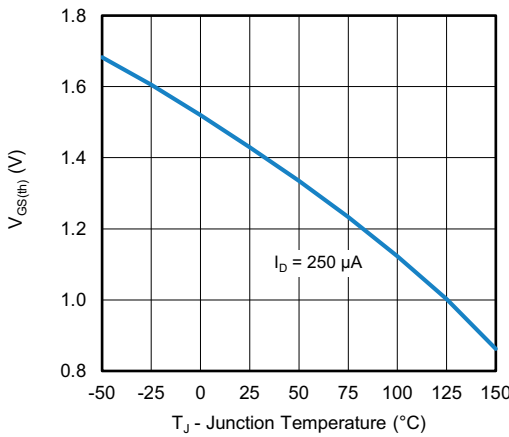
**CHANNEL-1 TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



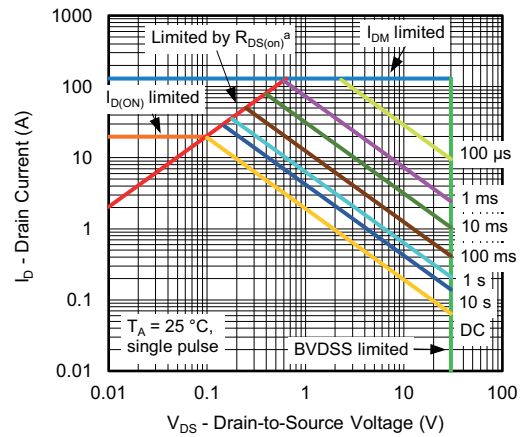
**Source-Drain Diode Forward Voltage**



**Single Pulse Power, Junction-to-Ambient**



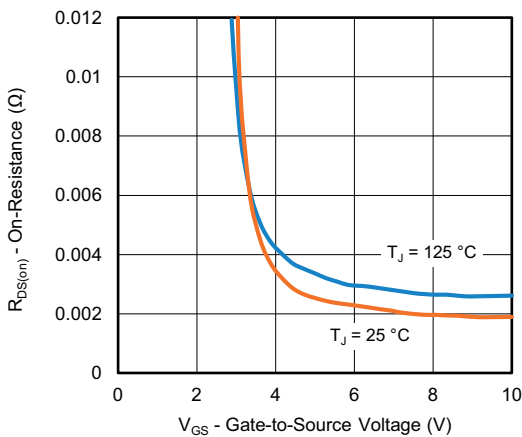
**Threshold Voltage**



**Safe Operating Area, Junction-to-Ambient**

**Note**

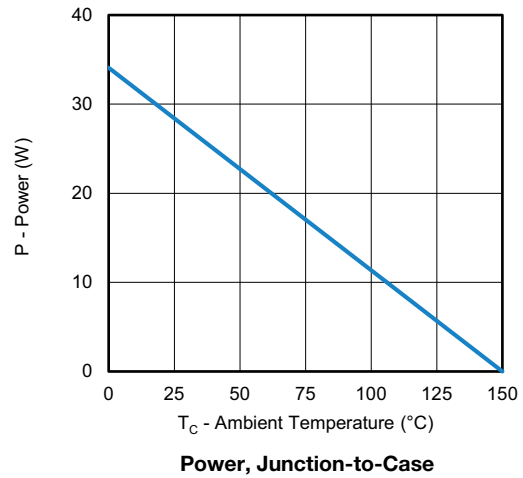
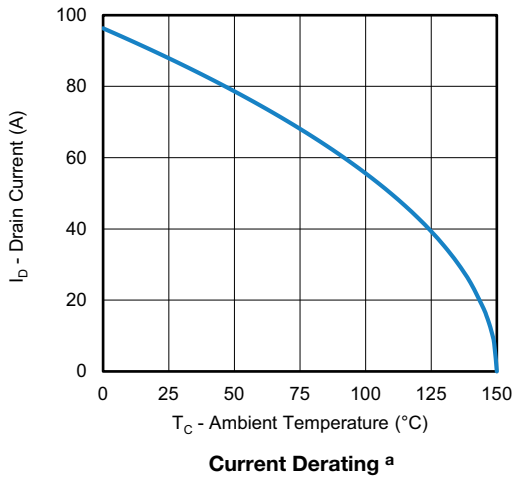
- a.  $V_{GS} >$  minimum  $V_{GS}$  at which  $R_{DS(on)}$  is specified



**On-Resistance vs. Gate-to-Source Voltage**



**CHANNEL-1 TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)

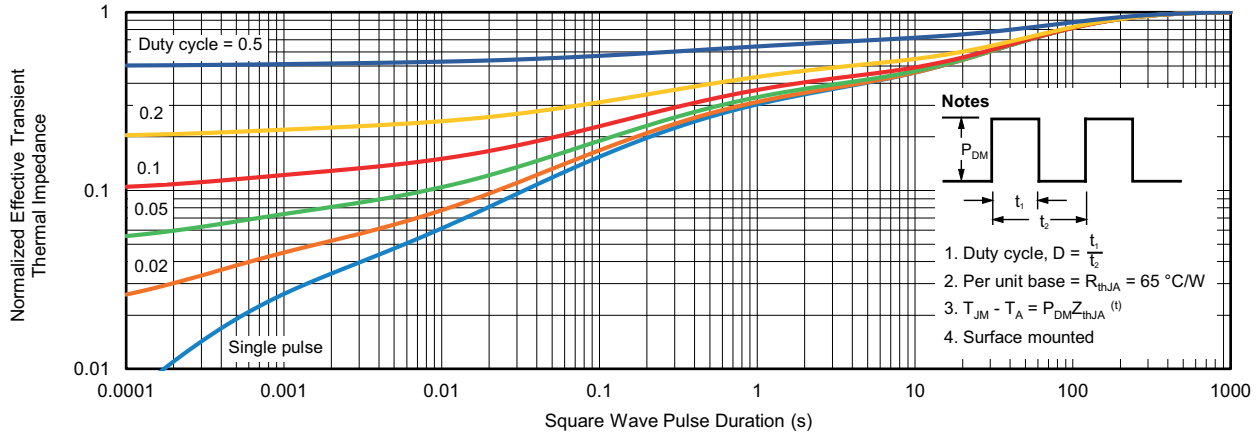


**Note**

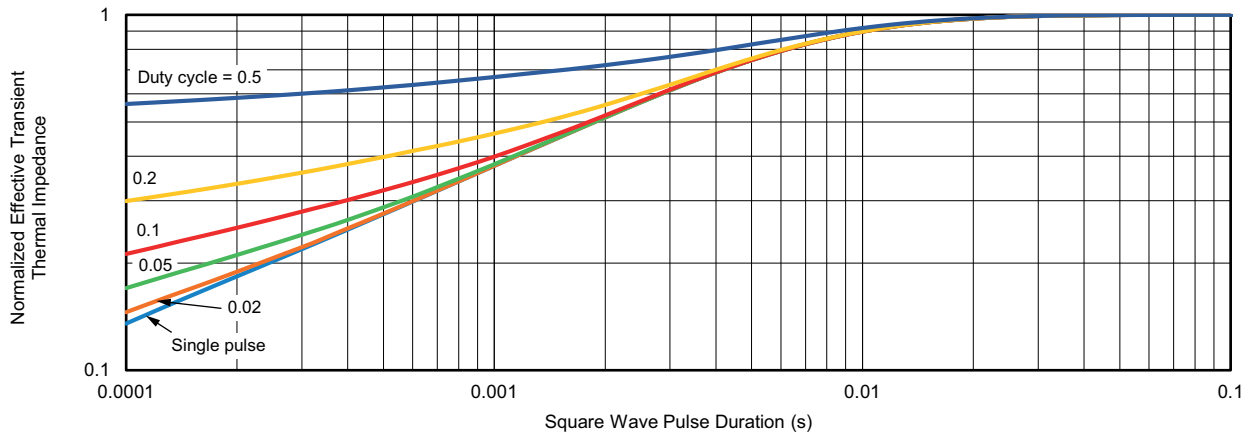
- a. The power dissipation  $P_D$  is based on  $T_J$  max. = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit



**CHANNEL-1 TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



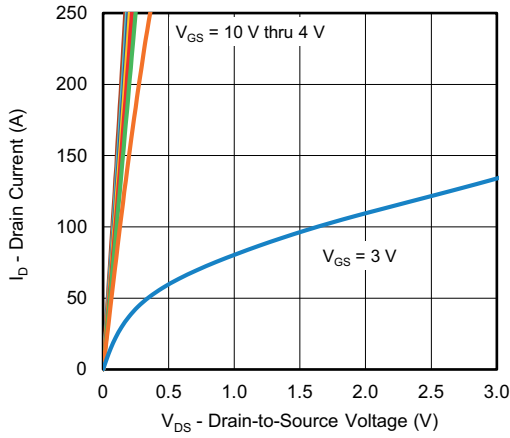
**Normalized Thermal Transient Impedance, Junction-to-Ambient**



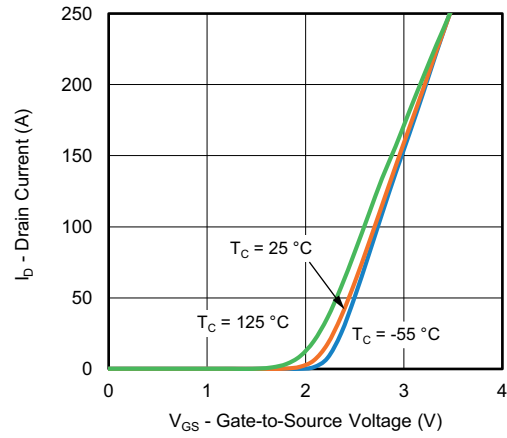
**Normalized Thermal Transient Impedance, Junction-to-Case**



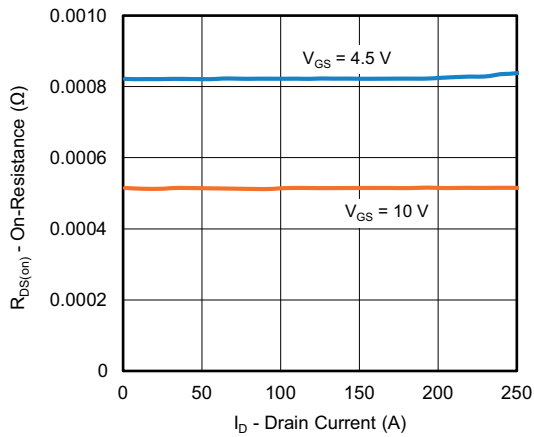
**CHANNEL-2 TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



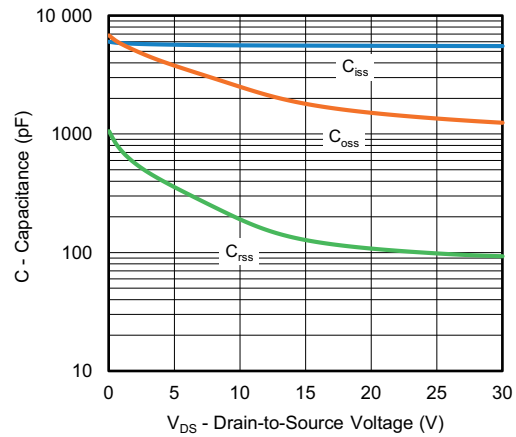
**Output Characteristics**



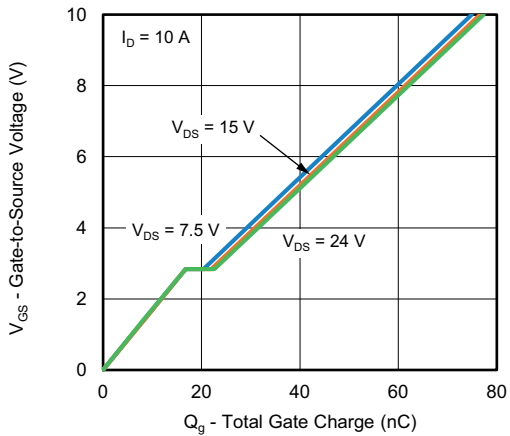
**Transfer Characteristics**



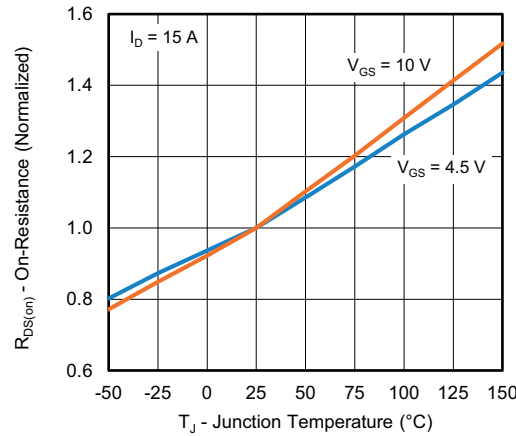
**On-Resistance vs. Drain Current**



**Capacitance**



**Gate Charge**

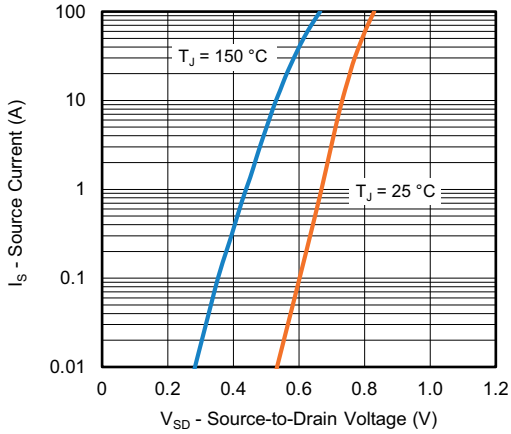


**On-Resistance vs. Junction Temperature**

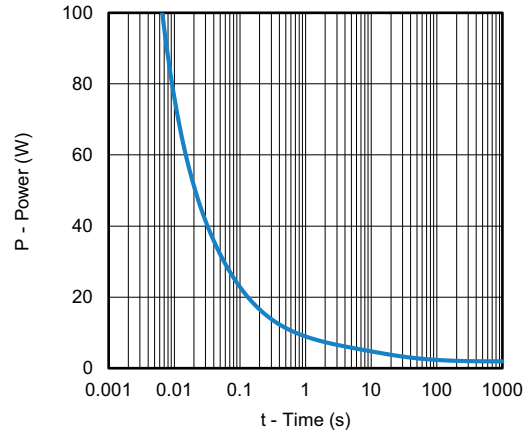




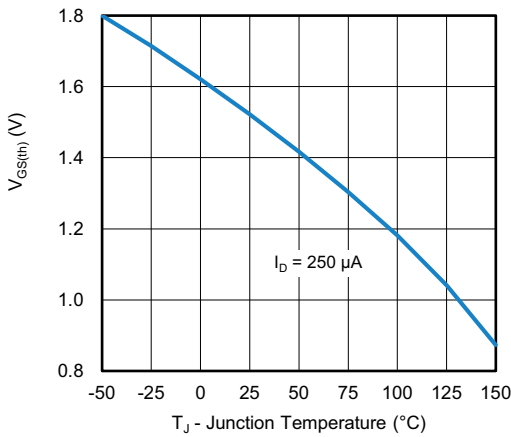
**CHANNEL-2 TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



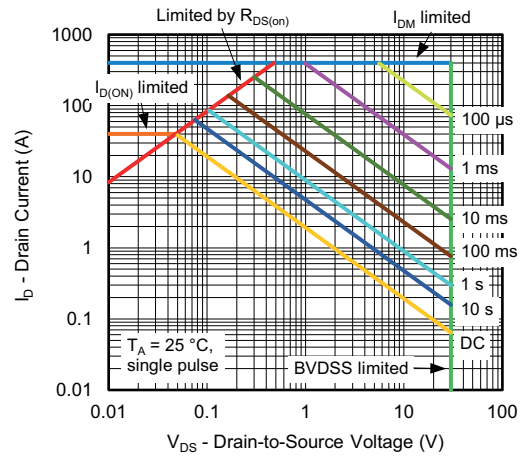
**Source-Drain Diode Forward Voltage**



**Single Pulse Power, Junction-to-Ambient**



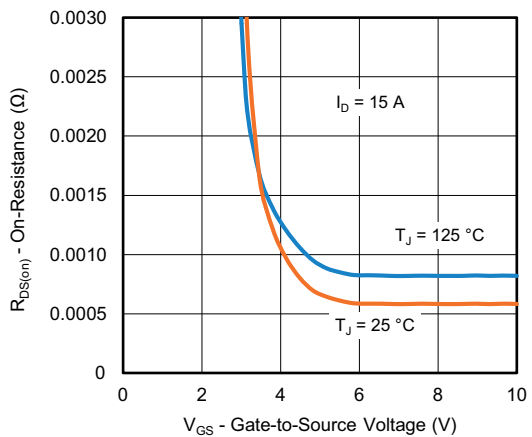
**Threshold Voltage**



**Safe Operating Area, Junction-to-Ambient**

**Note**

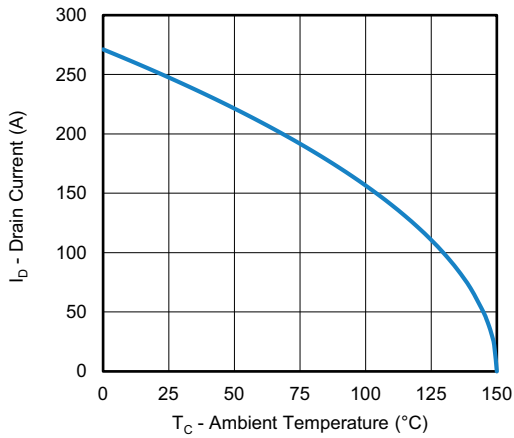
- a.  $V_{GS} >$  minimum  $V_{GS}$  at which  $R_{DS(on)}$  is specified



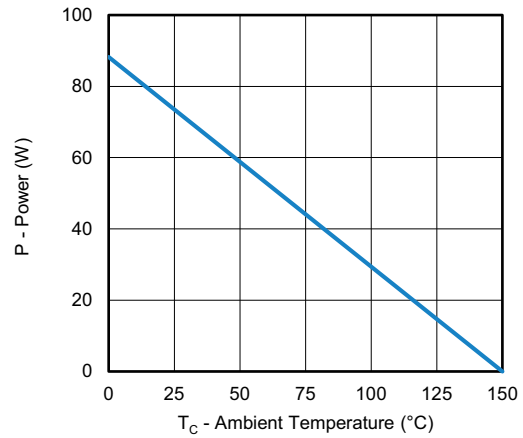
**On-Resistance vs. Gate-to-Source Voltage**



**CHANNEL-2 TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



**Current Derating <sup>a</sup>**



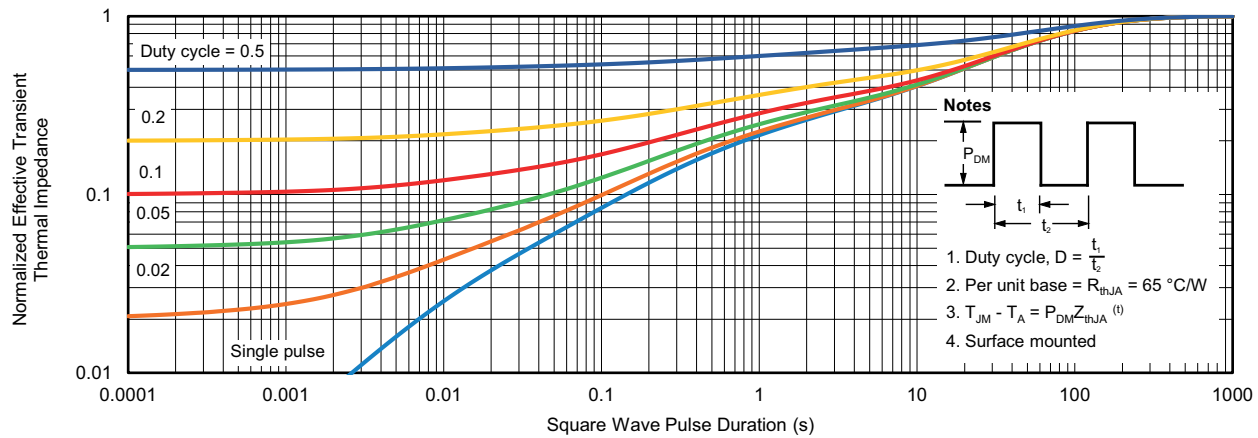
**Power, Junction-to-Case**

**Note**

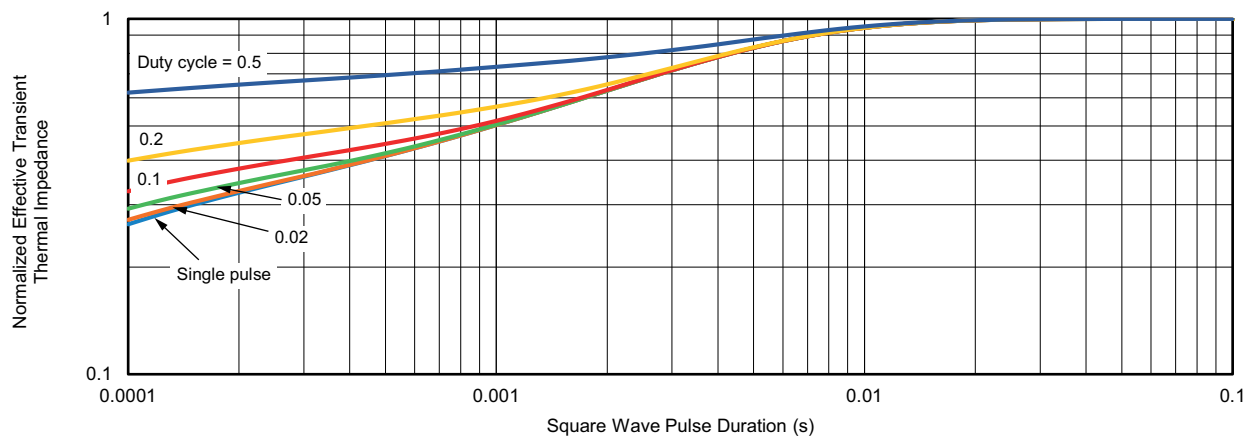
- a. The power dissipation  $P_D$  is based on  $T_J$  max. = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit



**CHANNEL-2 TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



**Normalized Thermal Transient Impedance, Junction-to-Ambient**



**Normalized Thermal Transient Impedance, Junction-to-Case**

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see [www.vishay.com/ppg?63037](http://www.vishay.com/ppg?63037).



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